

**SMBF Super Fast Recovery Diode 超快恢复二极管**

■ Features 特点

Fast Switching Speed 快的开关速度  
 Super Fast Recovery time 超快恢复时间  
 Glass passivated chip junction 玻璃钝化芯片保护结  
 Surface Mount Device 表面贴装器件  
 Case 封装:SMBF



■ Maximum Rating 最大额定值

( $T_A=25^{\circ}\text{C}$  unless otherwise noted 如无特殊说明, 温度为  $25^{\circ}\text{C}$ )

Characteristic 特性参数	Symbol 符号	ES3 ABF	ES3 BBF	ES3 CBF	ES3 DBF	ES3 EBF	ES3 GBF	ES3 JBF	Unit 单位
Repetitive Peak Reverse Voltage 重复峰值反向电压	$V_{RRM}$	50	100	150	200	300	400	600	V
DC Reverse Voltage 直流反向电压	$V_R$	50	100	150	200	300	400	600	V
RMS Reverse Voltage 反向电压均方根值	$V_{R(RMS)}$	35	70	105	140	210	280	420	V
Forward Rectified Current 正向整流电流	$I_F$	3							A
Peak Surge Current 峰值浪涌电流	$I_{FSM}$	80							A
Thermal Resistance J-A 结到环境热阻	$R_{\theta JA}$	90							$^{\circ}\text{C}/\text{W}$
Junction/Storage Temperature 结温/储藏温度	$T_J, T_{stg}$	-50to+150							$^{\circ}\text{C}$

■ Electrical Characteristics 电特性

( $T_A=25^{\circ}\text{C}$  unless otherwise noted 如无特殊说明, 温度为  $25^{\circ}\text{C}$ )

Characteristic 特性参数	Symbol 符号	ES3ABF-ES3DBF	ES3EBF-ES3GBF	ES3JBF	Unit 单位	Condition 条件
Forward Voltage 正向电压	$V_F$	0.95	1.25	1.7	V	$I_F=3\text{A}$
Reverse Current 反向电流	$I_R$	5( $T_A=25^{\circ}\text{C}$ ) 500( $T_A=100^{\circ}\text{C}$ )			$\mu\text{A}$	$V_R=V_{RRM}$
Reverse Recovery Time 反向恢复时间	$T_{rr}$	35			nS	$I_F=0.5\text{A}, I_R=1\text{A}$ $I_{rr}=0.25\text{A}$
Junction Capacitance 结电容	$C_J$	60			pF	$V_R=4\text{V}, f=1\text{MHz}$

■ Typical Characteristic Curve 典型特性曲线

FIG.1- TEST CIRCUIT DIAGRAM AND REVERSE RECOVERY TIME CHARACTERISTIC

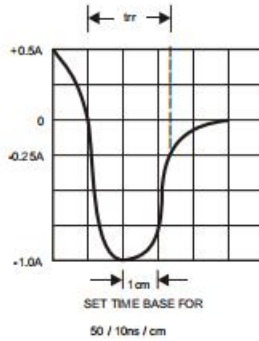
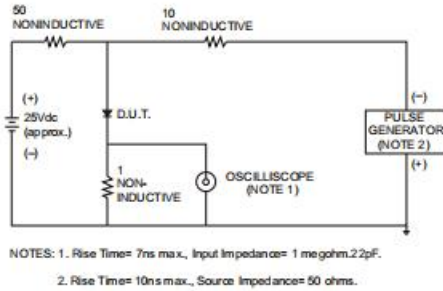


FIG.2-TYPICAL FORWARD CURRENT DERATING CURVE

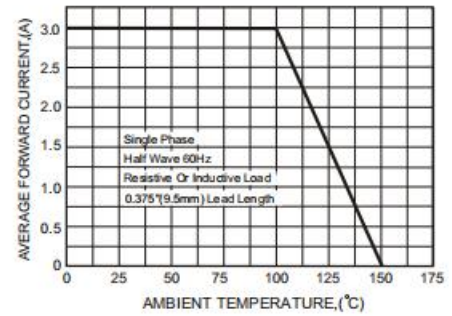


FIG.3-TYPICAL FORWARD CHARACTERISTICS

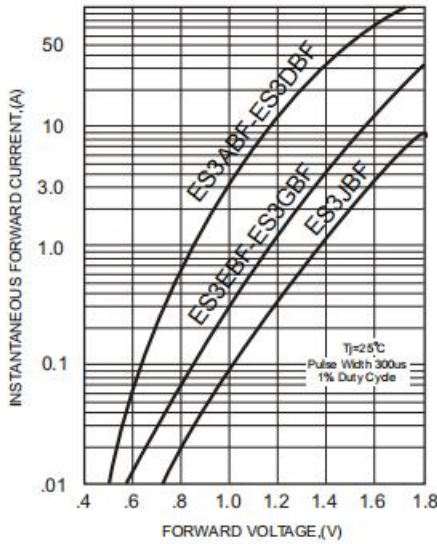


FIG.4-TYPICAL REVERSE CHARACTERISTICS

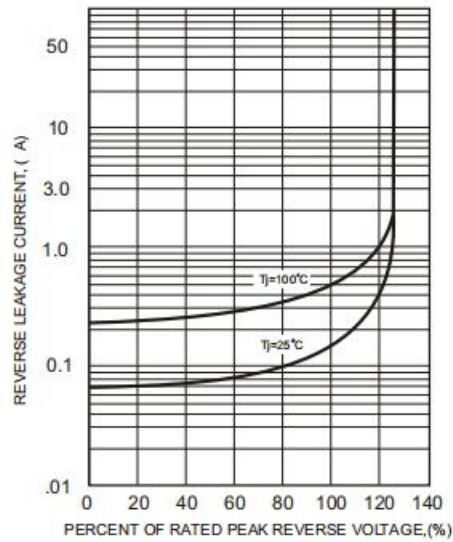


FIG.5-MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

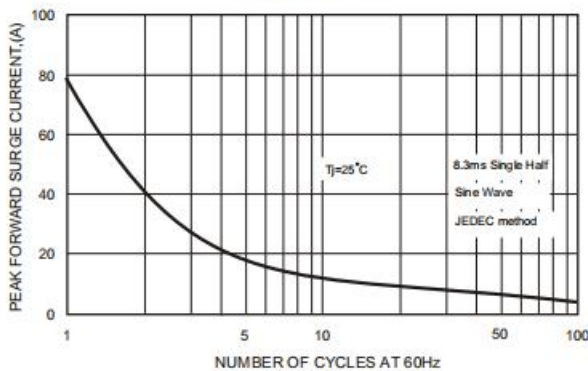
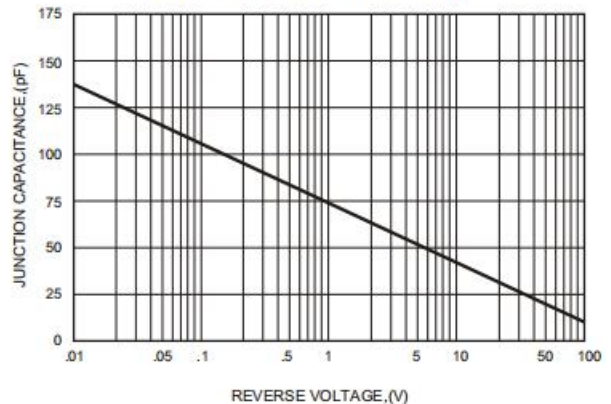


FIG.6-TYPICAL JUNCTION CAPACITANCE



■Dimension 外形封装尺寸

